



THE UNITED STATES PATENT AND TRADEMARK OFFICE

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TECHNOLOGY CENTER

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Applicants: MINAMI et al.
Serial No.: 09/768,471
Filed: January 25, 2001
For: SEMICONDUCTOR INTEGRATED CIRCUIT DEVICE
AND METHOD OF MANUFACTURING
Group: 2812
Examiner: R. Booth

SUPPLEMENTAL AMENDMENT

Assistant Commissioner
for Patents
Washington, D.C. 20231

October 26, 2001

Sir:

In supplement to the response filed on October 18, 2001,
please amend the above-identified application as follows:

In the Claims:

Please amend claims 1, 8, 11, 15, 16, 17, 19, 20 and 21 as
follows:

1. (Amended) A semiconductor integrated circuit device
comprising: a semiconductor substrate of a first conductivity
type; a zener diode comprised of a first semiconductor region
of a second conductivity type formed in a primary face of said
semiconductor substrate, and a second semiconductor region
that is of said first conductivity type formed in said
semiconductor substrate at a bottom portion of said first
semiconductor region and being smaller than said semiconductor

10/29/2001 AAD0F01 00000004 09768471

01 FC:102
02 FC:103

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